

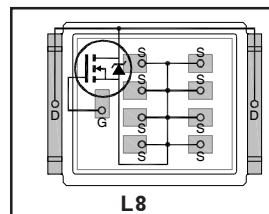
# AUIRF7759L2TR

## AUIRF7759L2TR1

Automotive DirectFET® Power MOSFET ②

- Advanced Process Technology
- Optimized for Automotive Motor Drive, DC-DC and other Heavy Load Applications
- Exceptionally Small Footprint and Low Profile
- High Power Density
- Low Parasitic Parameters
- Dual Sided Cooling
- 175°C Operating Temperature
- Repetitive Avalanche Capability for Robustness and Reliability
- Lead Free, RoHS Compliant and Halogen Free
- Automotive Qualified \*

$V_{(BR)DSS}$	<b>75V</b>
$R_{DS(on)}$ <b>typ.</b>	<b>1.8mΩ</b>
	<b>max.</b>
$I_D$ (Silicon Limited)	<b>160A</b>
$Q_g$	<b>200nC</b>



Applicable DirectFET® Outline and Substrate Outline ①

<b>SB</b>	<b>SC</b>			<b>M2</b>	<b>M4</b>		<b>L4</b>	<b>L6</b>	<b>L8</b>
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### Description

The AUIRF7759L2TR(1) combines the latest Automotive HEXFET® Power MOSFET Silicon technology with the advanced DirectFET® packaging to achieve the lowest on-state resistance in a package that has the footprint of a DPak (TO-252AA) and only 0.7 mm profile. The DirectFET® package is compatible with existing layout geometries used in power applications, PCB assembly equipment and vapor phase, infra-red or convection soldering techniques, when application note AN-1035 is followed regarding the manufacturing methods and processes. The DirectFET® package allows dual sided cooling to maximize thermal transfer in automotive power systems.

This HEXFET® Power MOSFET is designed for applications where efficiency and power density are essential. The advanced DirectFET® packaging platform coupled with the latest silicon technology allows the AUIRF7759L2TR(1) to offer substantial system level savings and performance improvement specifically in motor drive, high frequency DC-DC and other heavy load applications on ICE, HEV and EV platforms. This MOSFET utilizes the latest processing techniques to achieve low on-resistance and low Qg per silicon area. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for high current automotive applications.

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	75	V
$V_{GS}$	Gate-to-Source Voltage	±20	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)④	160	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)④	113	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)③	26	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited) ④	375	
$I_{DM}$	Pulsed Drain Current ⑤	640	
$P_D @ T_C = 25^\circ C$	Power Dissipation ④	125	W
$P_D @ T_C = 100^\circ C$	Power Dissipation ④	63	
$P_D @ T_A = 25^\circ C$	Power Dissipation ①	3.3	
$E_{AS}$	Single Pulse Avalanche Energy ⑥	257	mJ
$I_{AR}$	Avalanche Current ⑤	See Fig.18a, 18b, 16, 17	A
$E_{AR}$	Repetitive Avalanche Energy ⑤		mJ
$T_P$	Peak Soldering Temperature	270	°C
$T_J$	Operating Junction and	-55 to + 175	
$T_{STG}$	Storage Temperature Range		

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③	—	45	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⑧	12.5	—	
$R_{\theta JA}$	Junction-to-Ambient ⑨	20	—	
$R_{\theta J-Can}$	Junction-to-Can ④⑩	—	1.2	
$R_{\theta J-PCB}$	Junction-to-PCB Mounted	—	0.5	
	Linear Derating Factor ④	0.83		W/°C

HEXFET® is a registered trademark of International Rectifier.

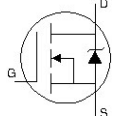
## Static Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

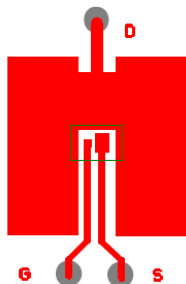
	Parameter	Min.	Typ.	Max.	Units	Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	75	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 2mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.8	2.3	m $\Omega$	$V_{GS} = 10V, I_D = 96A$ ⑦
$V_{GS(th)}$	Gate Threshold Voltage	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-11	—	mV/ $^\circ\text{C}$	
$g_{fs}$	Forward Transconductance	74	—	—	S	$V_{DS} = 25V, I_D = 96A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 75V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 60V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

## Dynamic Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

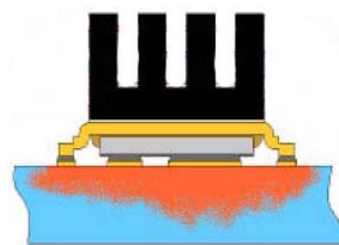
$Q_g$	Total Gate Charge	—	200	300	nC	$V_{DS} = 38V$ $V_{GS} = 10V$ $I_D = 96A$ See Fig. 9
$Q_{gs1}$	Pre-V <sub>th</sub> Gate-to-Source Charge	—	37	—		
$Q_{gs2}$	Post-V <sub>th</sub> Gate-to-Source Charge	—	11	—		
$Q_{gd}$	Gate-to-Drain Charge	—	62	93		
$Q_{godr}$	Gate Charge Overdrive	—	91	—		
$Q_{sw}$	Switch Charge ( $Q_{gs2} + Q_{gd}$ )	—	73	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
$Q_{oss}$	Output Charge	—	60	—		
$R_G$	Gate Resistance	—	1.1	—	$\Omega$	
$t_{d(on)}$	Turn-On Delay Time	—	18	—	ns	$V_{DD} = 38V, V_{GS} = 10V$ ⑦ $I_D = 96A$ $R_G = 1.8\Omega$
$t_r$	Rise Time	—	37	—		
$t_{d(off)}$	Turn-Off Delay Time	—	80	—		
$t_f$	Fall Time	—	33	—		
$C_{iss}$	Input Capacitance	—	12222	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0MHz$ $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$ $V_{GS} = 0V, V_{DS} = 60V, f = 1.0MHz$
$C_{oss}$	Output Capacitance	—	1465	—		
$C_{rss}$	Reverse Transfer Capacitance	—	609	—		
$C_{oss}$	Output Capacitance	—	7457	—		
$C_{oss}$	Output Capacitance	—	955	—		

## Diode Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

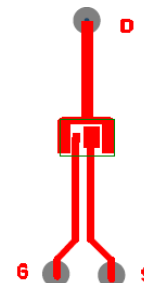
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	160	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ⑤	—	—	640		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 96A, V_{GS} = 0V$ ⑦
$t_{rr}$	Reverse Recovery Time	—	64	96	ns	$T_J = 25^\circ\text{C}, I_F = 96A, V_{DD} = 38V$
$Q_{rr}$	Reverse Recovery Charge	—	150	225	nC	$di/dt = 100A/\mu s$ ⑦



③ Surface mounted on 1 in. square Cu (still air).



⑨ Mounted to a PCB with small clip heatsink (still air)



⑩ Mounted on minimum footprint full size board with metalized back and with small clip heatsink (still air)

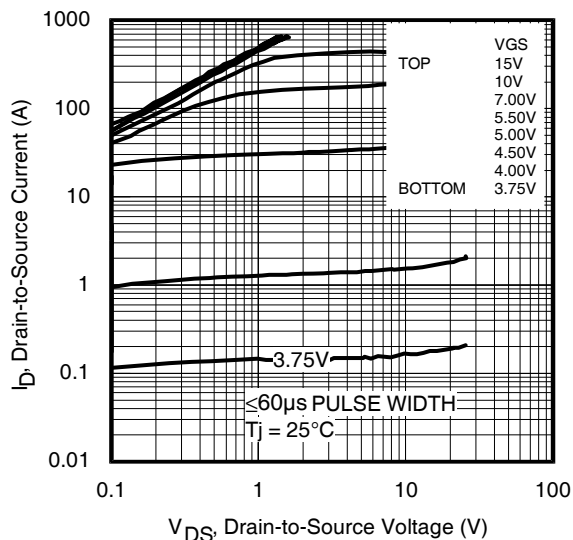
Notes ① through ⑩ are on page 10

## Qualification Information<sup>†</sup>

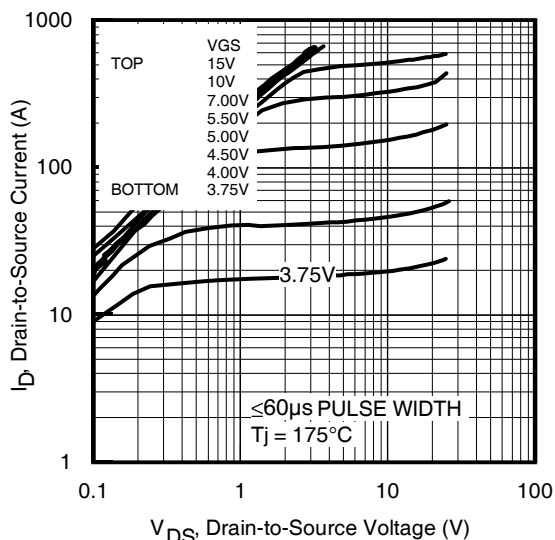
<b>Qualification Level</b>		Automotive (per AEC-Q101) <sup>††</sup>	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		LARGE-CAN	MSL1
<b>ESD</b>	Machine Model	Class M4 (+/- 800V) (per AEC-Q101-002)	
	Human Body Model	Class H2 (+/- 6000V) (per AEC-Q101-001)	
	Charged Device Model	N/A (per AEC-Q101-005)	
<b>RoHS Compliant</b>		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

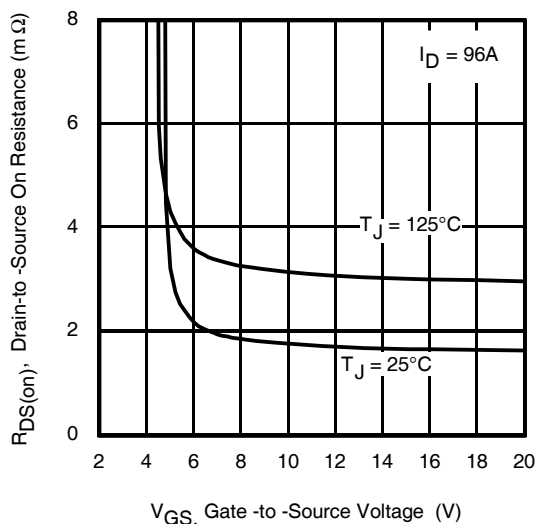
†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.



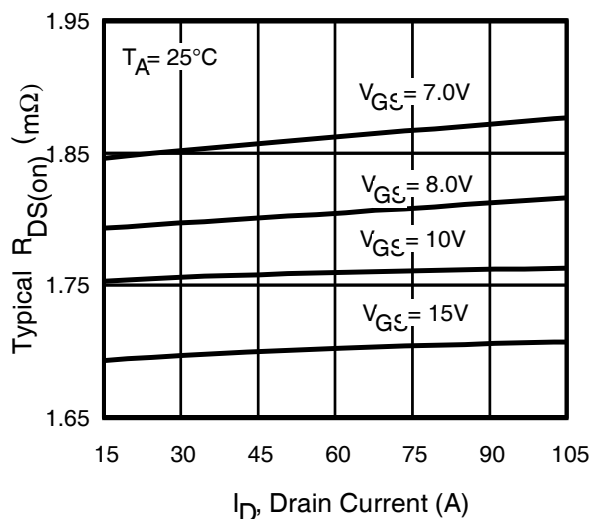
**Fig 1.** Typical Output Characteristics



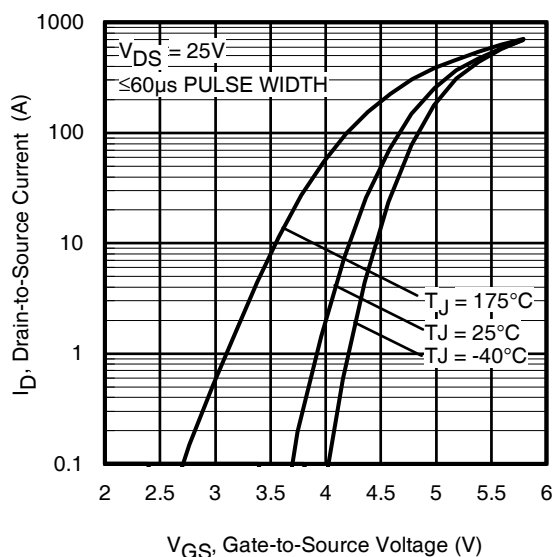
**Fig 2.** Typical Output Characteristics



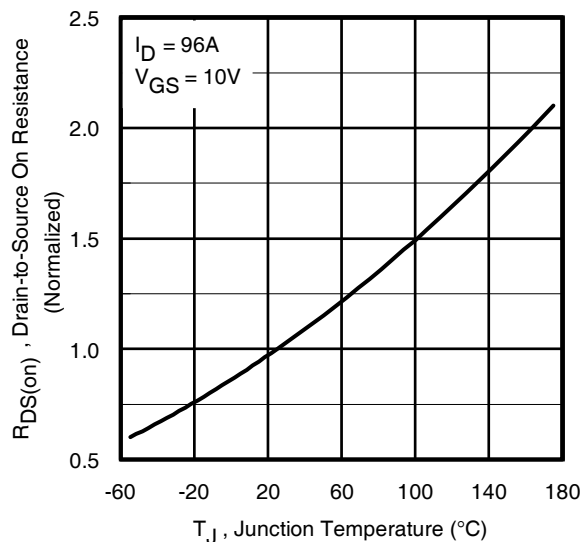
**Fig 3.** Typical On-Resistance vs. Gate Voltage



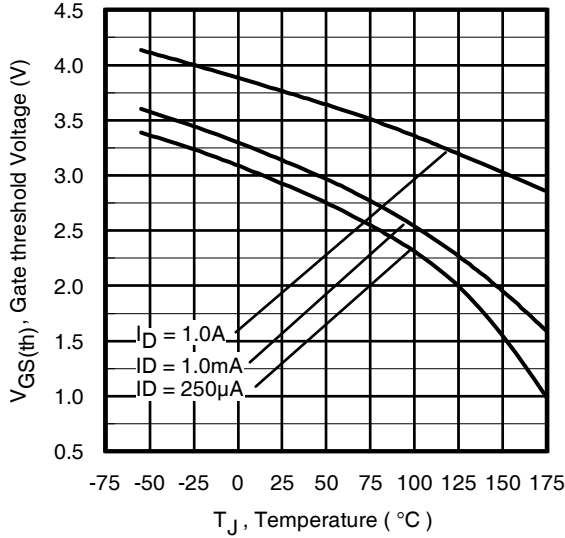
**Fig 4.** Typical On-Resistance vs. Drain Current



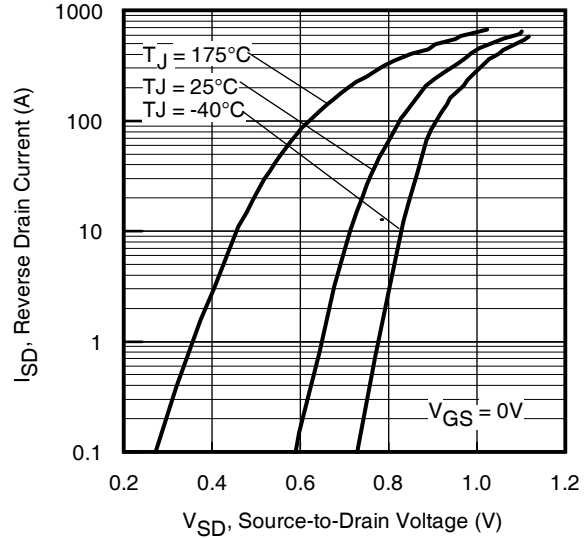
**Fig 5.** Typical Transfer Characteristics



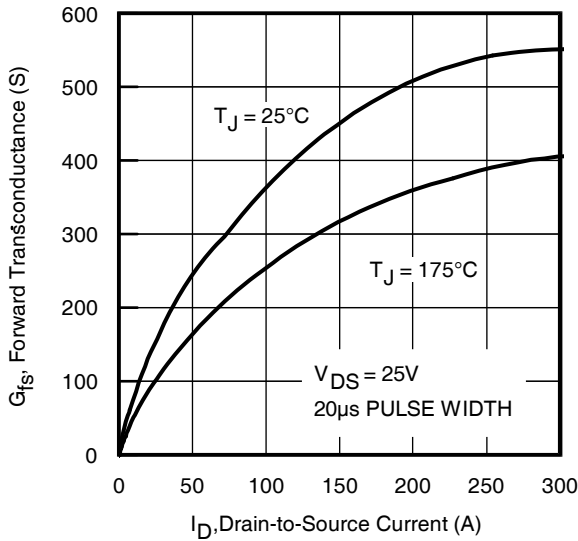
**Fig 6.** Normalized On-Resistance vs. Temperature



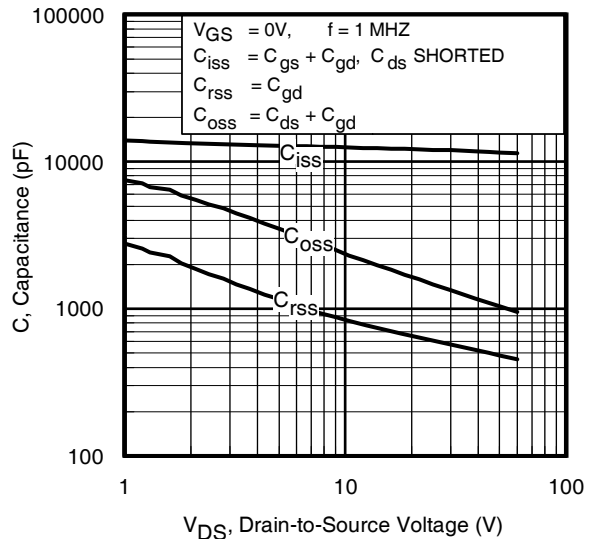
**Fig 7.** Typical Threshold Voltage vs. Junction Temperature



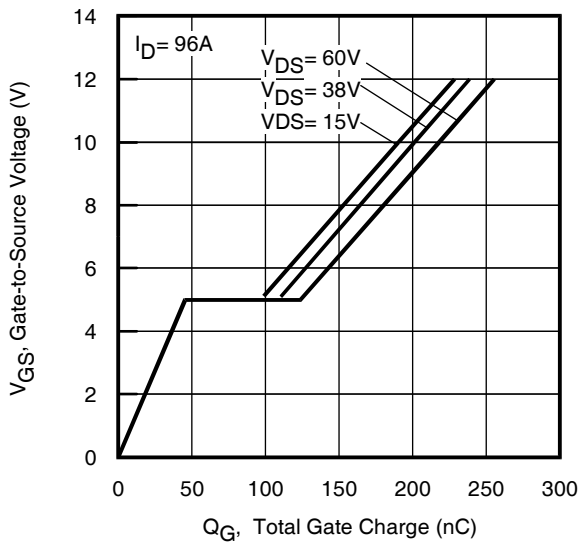
**Fig 8.** Typical Source-Drain Diode Forward Voltage



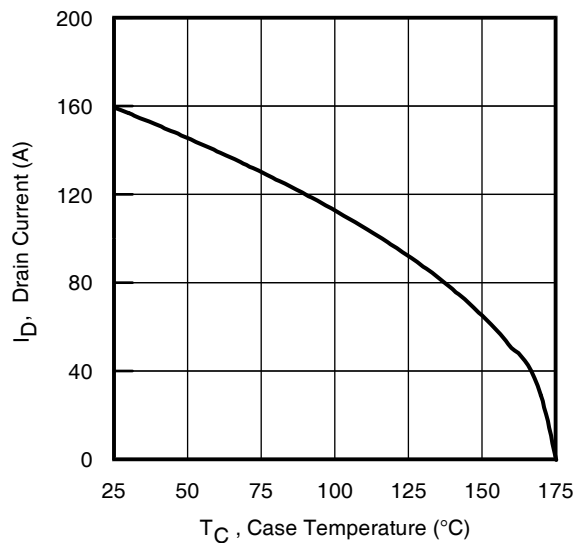
**Fig 9.** Typical Forward Transconductance vs. Drain Current



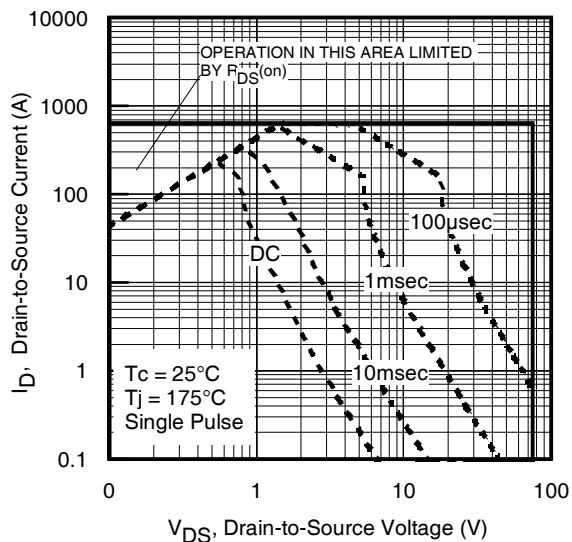
**Fig 10.** Typical Capacitance vs. Drain-to-Source Voltage



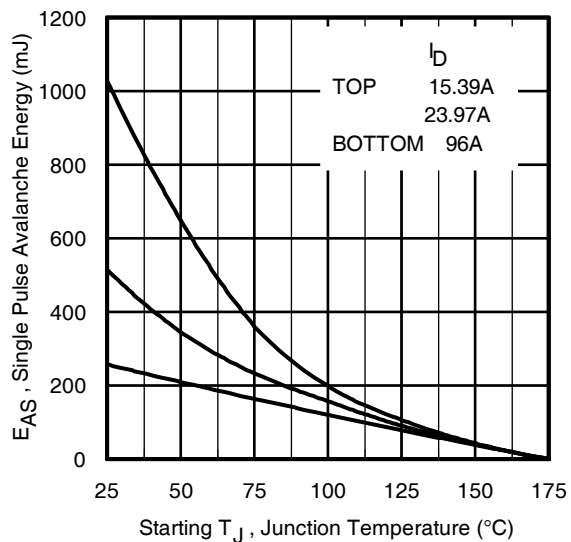
**Fig.11** Typical Gate Charge vs. Gate-to-Source Voltage



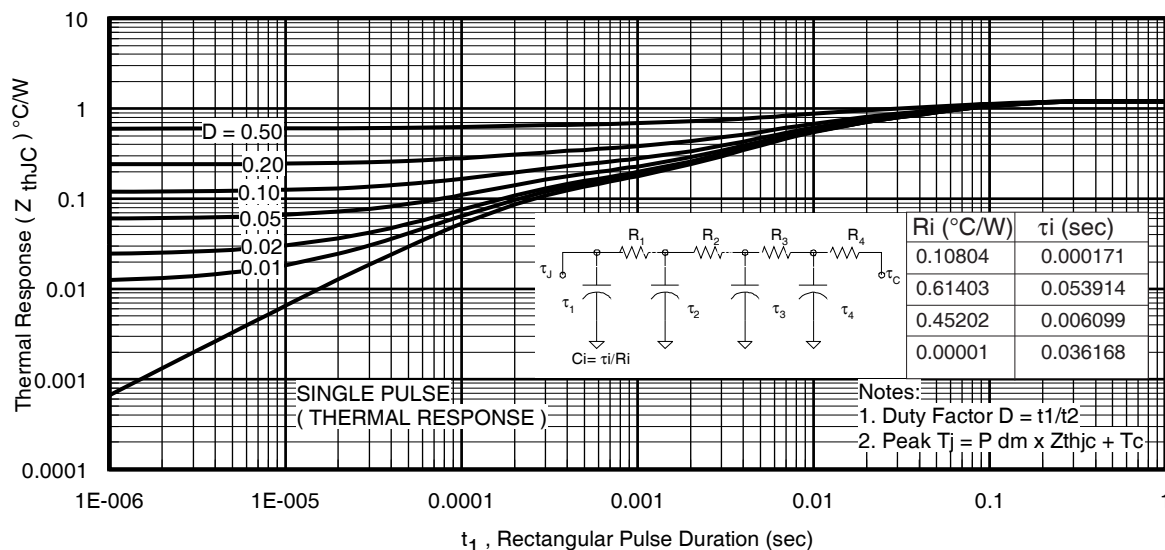
**Fig 12.** Maximum Drain Current vs. Case Temperature



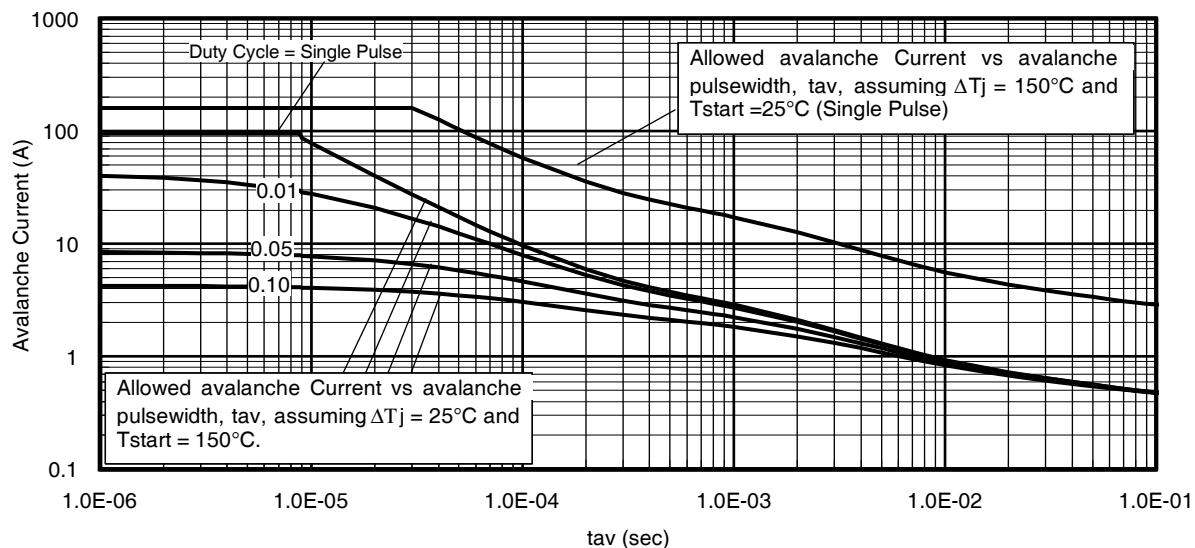
**Fig 13.** Maximum Safe Operating Area



**Fig 14.** Maximum Avalanche Energy vs. Temperature



**Fig 15.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



**Fig 16.** Typical Avalanche Current vs. Pulsewidth

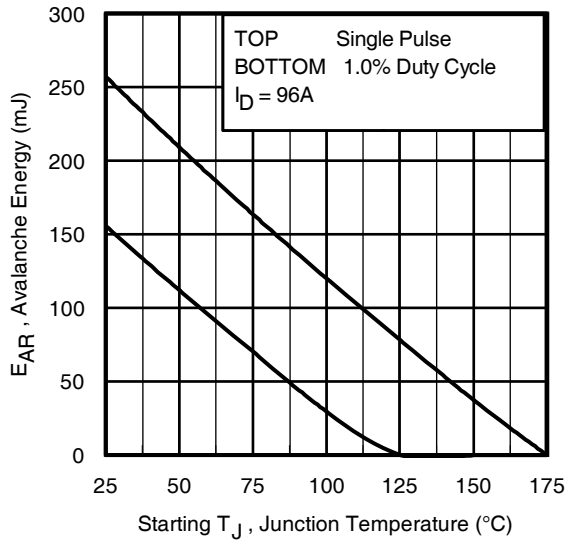


Fig 17. Maximum Avalanche Energy vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 14, 17:**  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 18a, 18b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

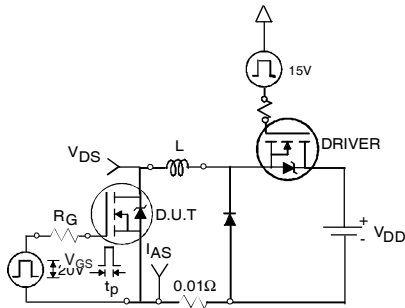


Fig 18a. Unclamped Inductive Test Circuit

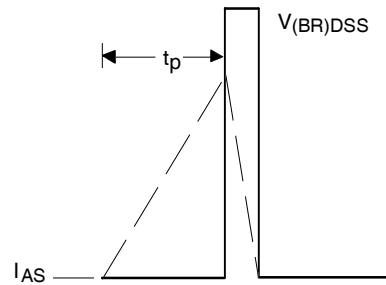


Fig 18b. Unclamped Inductive Waveforms

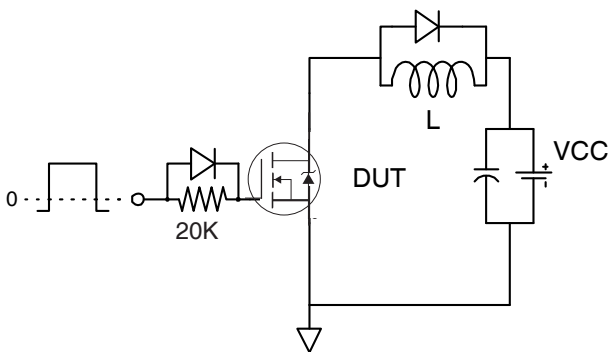


Fig 19a. Gate Charge Test Circuit

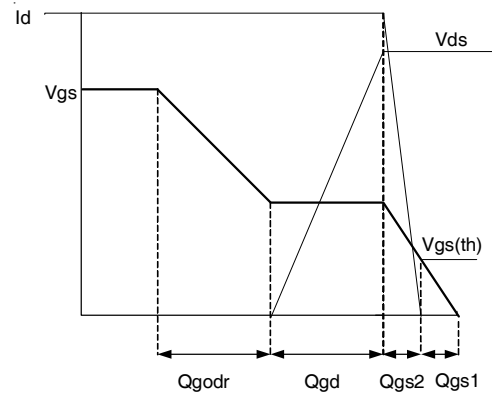


Fig 19b. Gate Charge Waveform

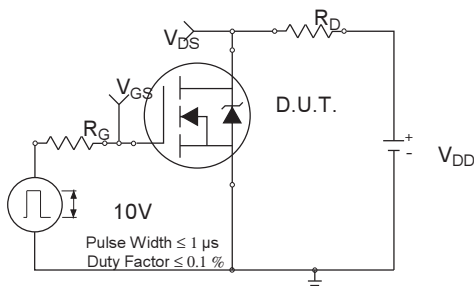


Fig 20a. Switching Time Test Circuit

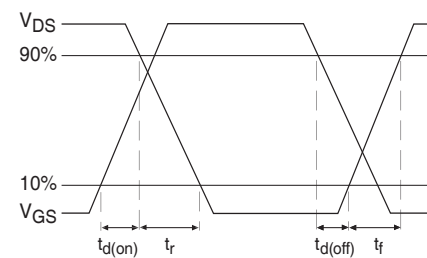
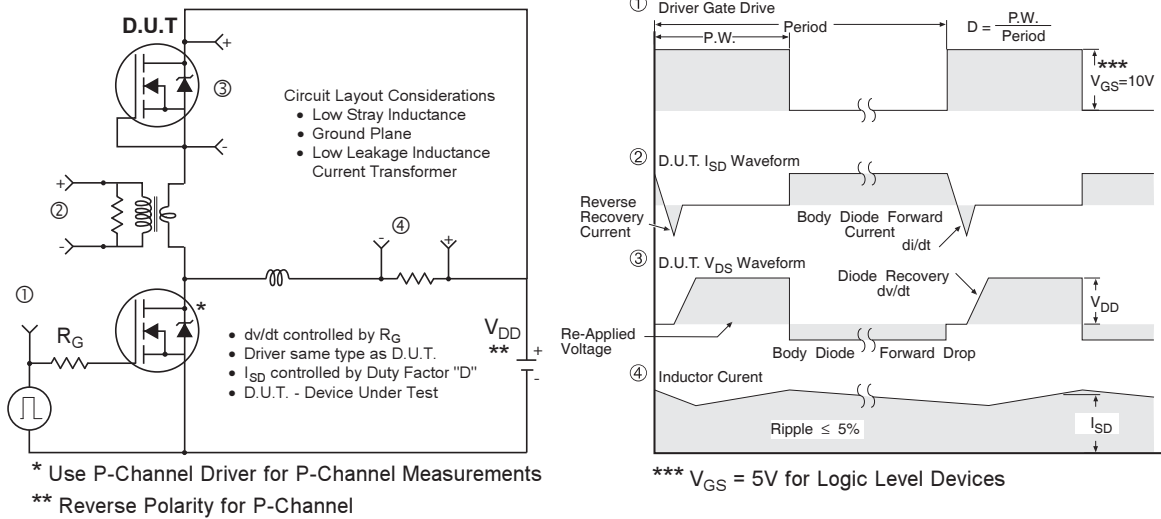


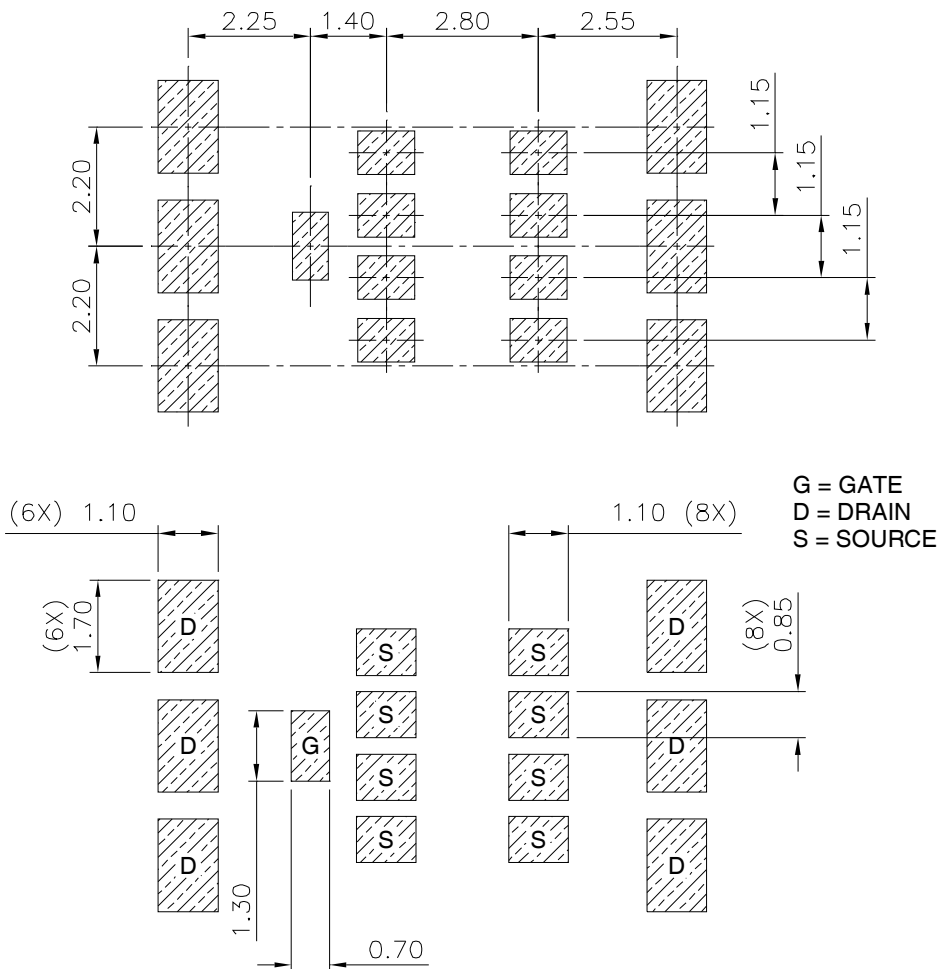
Fig 20b. Switching Time Waveforms



**Fig 21. Diode Reverse Recovery Test Circuit for HEXFET® Power MOSFETs**

## Automotive DirectFET® Board Footprint, L8 (Large Size Can).

Please see AN-1035 for DirectFET® assembly details and stencil and substrate design recommendations

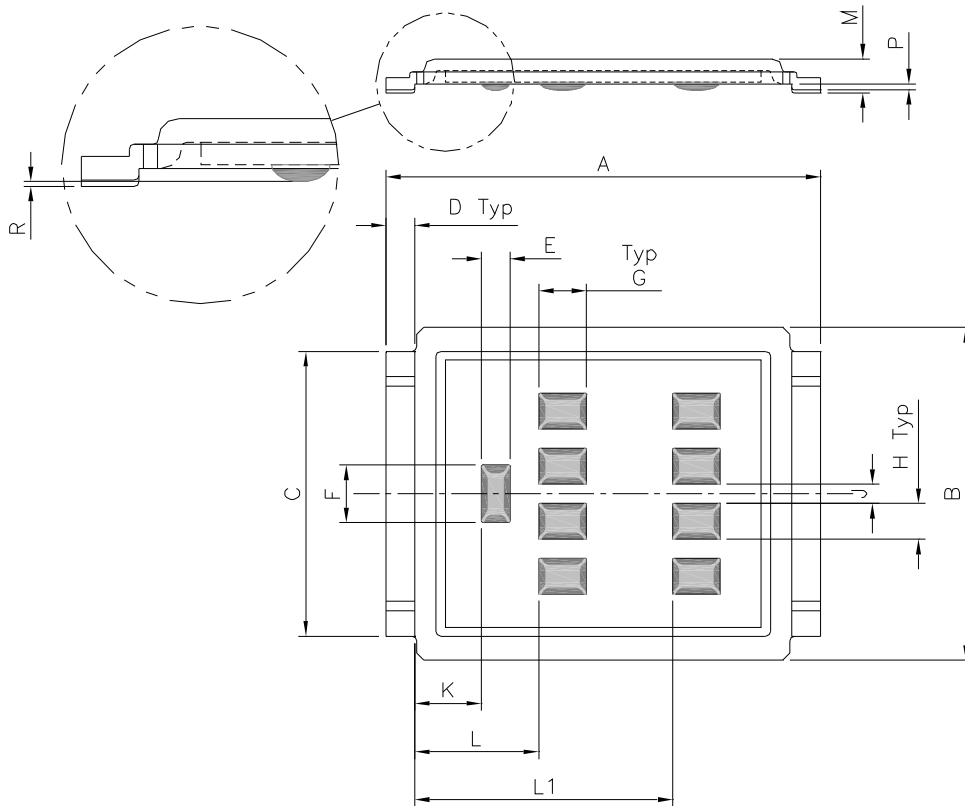


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>



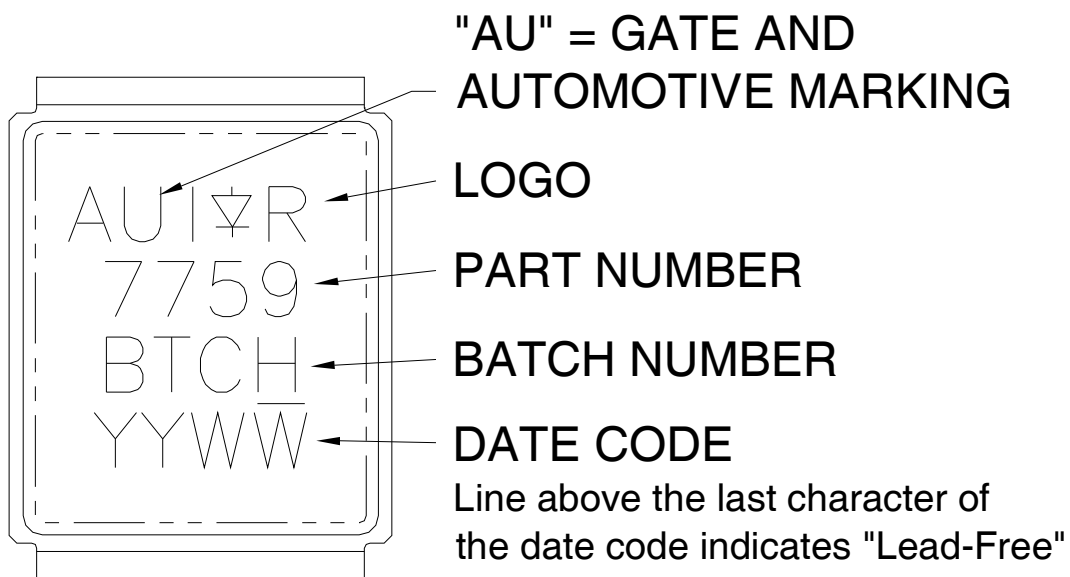
## Automotive DirectFET® Outline Dimension, L8 Outline (LargeSize Can).

Please see AN-1035 for DirectFET® assembly details and stencil and substrate design recommendations



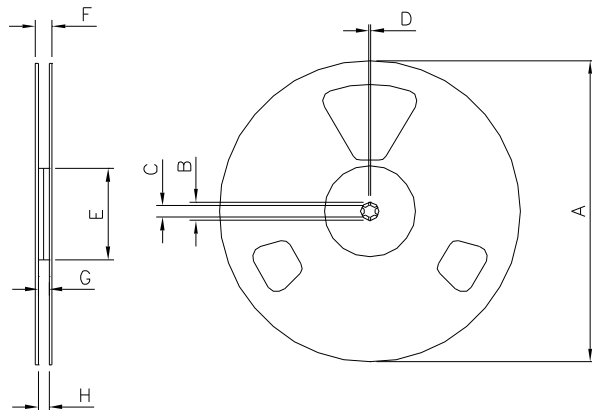
CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	9.05	9.15	0.356	0.360
B	6.85	7.10	0.270	0.280
C	5.90	6.00	0.232	0.236
D	0.55	0.65	0.022	0.026
E	0.58	0.62	0.023	0.024
F	1.18	1.22	0.046	0.048
G	0.98	1.02	0.039	0.040
H	0.73	0.77	0.029	0.030
J	0.38	0.42	0.015	0.017
K	1.35	1.45	0.053	0.057
L	2.55	2.65	0.100	0.104
L1	5.35	5.45	0.211	0.215
M	0.68	0.74	0.027	0.029
P	0.09	0.17	0.003	0.007
R	0.02	0.08	0.001	0.003

## Automotive DirectFET® Part Marking



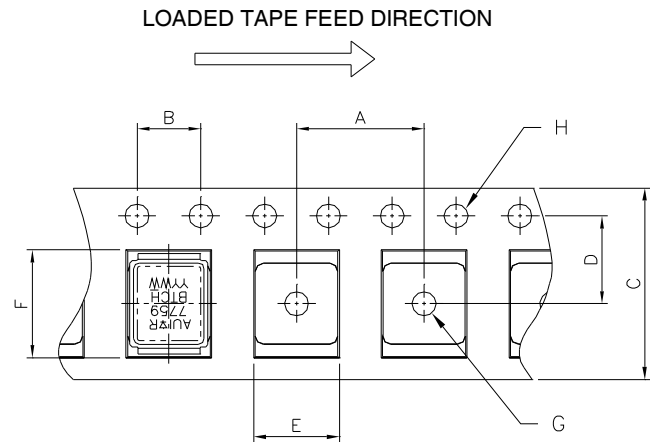
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>  
[www.irf.com](http://www.irf.com)

## Automotive DirectFET® Tape & Reel Dimension (Showing component orientation).



NOTE: Controlling dimensions in mm  
Std reel quantity is 4000 parts. (ordered as AUIRF7759L2TR). For 1000 parts on 7" reel, order AUIRF7759L2TR1

REEL DIMENSIONS								
CODE	STANDARD OPTION (QTY 4000)				TR1 OPTION (QTY 1000)			
	METRIC		IMPERIAL		METRIC		IMPERIAL	
A	330.00	N.C	12.992	N.C	177.80	N.C	7.000	N.C
B	20.20	N.C	0.795	N.C	20.20	N.C	0.795	N.C
C	12.80	13.20	0.504	0.520	12.98	13.50	0.331	0.50
D	1.50	N.C	0.059	N.C	1.50	2.50	0.059	N.C
E	99.00	100.00	3.900	3.940	62.48	N.C	2.460	N.C
F	N.C	22.40	N.C	0.880	N.C	N.C	N.C	0.53
G	16.40	18.40	0.650	0.720	N.C	N.C	N.C	N.C
H	15.90	19.40	0.630	0.760	16.00	N.C	0.630	N.C



NOTE: CONTROLLING DIMENSIONS IN MM

CODE	DIMENSIONS			
	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	11.90	12.10	4.69	0.476
B	3.90	4.10	0.154	0.161
C	15.90	16.30	0.623	0.642
D	7.40	7.60	0.291	0.299
E	7.20	7.40	0.283	0.291
F	9.90	10.10	0.390	0.398
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

### Notes:

- ① Click on this section to link to the appropriate technical paper.
- ② Click on this section to link to the DirectFET® Website.
- ③ Surface mounted on 1 in. square Cu board, steady state.
- ④  $T_C$  measured with thermocouple mounted to top (Drain) of part.
- ⑤ Repetitive rating; pulse width limited by max. junction temperature.
- ⑥ Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.056\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 96\text{A}$ .
- ⑦ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑧ Used double sided cooling, mounting pad with large heatsink.
- ⑨ Mounted on minimum footprint full size board with metalized back and with small clip heatsink.
- ⑩  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .

## Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF7759L2	DirectFET2 Large Can	Tape and Reel	4000	AUIRF7759L2TR
		Tape and Reel	1000	AUIRF7759L2TR1

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For technical support, please contact IR's Technical Assistance Center  
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